









# B2D08065KS

## 650V ▲ 8A ▲ SiC SCHOTTKY DIODE

SILICON CARBIDE SIC SCHOTTKY DIODE ▲ THT type

Excellent surge capability

Easy paralleling due to positive V<sub>F</sub> temperature coefficient

Temperature independent switching

Ultra-low forward voltage and high surge current

TO-220 ISO-2L ceramic package ▲ 2.5kV isolation voltage

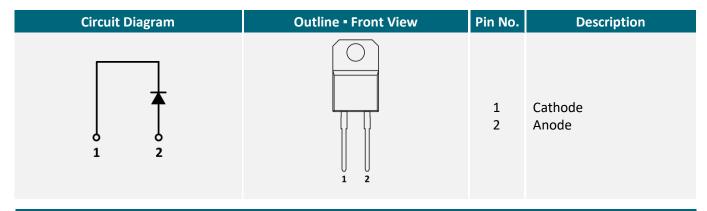
# **SPECIFICATION**

Item (T <sub>c</sub> = 25°C, unless otherwise noted)		Characteristics
Operating Temperature Range	Tı	-55°C to +175°C
Storage Temperature Range	Ts	-55°C to +175°C
Repetitive Peak Reverse Voltage	$V_{RRM}$	650V
Continuous Forward Current at T <sub>C</sub> = 150°C	I <sub>F</sub>	8A
Total Capacitive Charge (T <sub>J</sub> = 25°C)	$\mathbf{Q}_{c}$	24nC
Capacitance Stored Energy (V <sub>R</sub> = 400V)	Ec	6µЈ
Diode Forward Voltage (T <sub>J</sub> = 175°C, I <sub>F</sub> = 8A)	V <sub>F</sub>	1.54V
Power Dissipation	P <sub>TOT</sub>	86W

#### **APPLICATIONS**

EV Charging	Industrial Inverters	Motors & Drives	Power Factor Correction	Renewable Energy	SMPS	UPS
<b>₹</b> ¶ <b>#</b>			PFC	*		

## **PIN DESCRIPTION**



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# ABSOLUT MAXIMUM RATINGS ▲ T<sub>C</sub> = 25°C, unless otherwise noted

ltem	Condition	Symbol		Unit
Repetitive Peak Reverse Voltage		$V_{RRM}$	650	V
Non-Repetitive Peak Reverse Voltage		$V_{RSM}$	650	V
Continuous Forward Current	T <sub>C</sub> = 25°C	I <sub>F</sub>	26	Α
Continuous Forward Current	T <sub>C</sub> = 150°C	I <sub>F</sub>	8	Α
Non-Repetitive Forward Surge Current	$T_C = 25$ °C, $t_p = 10$ ms, Half Sine Wave	I <sub>FSM</sub>	64	Α
I <sup>2</sup> t Value	$T_C = 25^{\circ}C$ , $t_p = 10$ ms	∫i²dt	20.48	$A^2s$
Power Dissipation	T <sub>C</sub> = 25°C	P <sub>TOT</sub>	86	W
Power Dissipation	T <sub>C</sub> = 110°C	$P_{TOT}$	37	W
Operating Junction Temperature		TJ	-55 to +175	°C
Storage Temperature Range		$T_{STG}$	-55 to +175	°C
Isolation Voltage	AC, t = 1s	V <sub>ISOL</sub>	2500	$V_{RMS}$
TO-220 Mounting Torque	M3 Screw		0.7	Nm

# **ELECTRICAL CHARACTERISTICS**

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Static Characteristics						
DC Blocking Voltage	T <sub>J</sub> = 25°C	$V_{DC}$	650			V
Diode Forward Voltage	$I_F = 8A, T_J = 25^{\circ}C$	$V_{F}$		1.28		V
Diode Forward Voltage	$I_F = 8A, T_J = 175^{\circ}C$	$V_{F}$		1.54		V
Reverse Current	$V_R = 650V, T_J = 25^{\circ}C$	$I_R$		1		μΑ
Reverse Current	$V_R = 650V$ , $T_J = 175$ °C	I <sub>R</sub>		10		μΑ
ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Dynamic Characteristics	Containen	o y moor		. ) [5.	Total	0
Total Capacitive Charge	$V_{R} = 400V, T_{J} = 25^{\circ}C$ $Q_{C} = \int_{0}^{V_{R}} C(V) dV$	$Q_{C}$		24		nC
Total Capacitance	$V_R = 1V$ , $f = 1MHz$ , $T_J = 25$ °C	С		365		рF
Total Capacitance	$V_R = 300V, f = 1MHz, T_J = 25^{\circ}C$	С		41.1		pF
Total Capacitance	$V_R = 600V$ , $f = 1MHz$ , $T_J = 25$ °C	С		40.7		pF
Capacitance Stored Energy	$V_R = 400V, T_J = 25^{\circ}C$	E <sub>C</sub>		6		μЈ

## THERMAL RESISTANCE PERFORMANCE

Item	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance, Junction to Case	$R_{\theta,JC}$		1.730		K/W



#### REFERENCE DATA A TYPICAL PERFORMANCE

Fig. 1 • Typical Forward Characteristics I<sub>F</sub> vs. V<sub>F</sub>

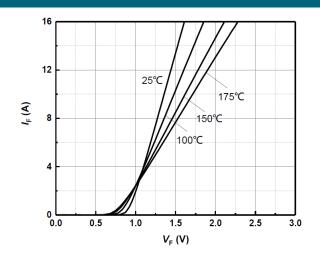


Fig. 2 • Typical Reverse Current I<sub>R</sub> as function of Reverse Voltage V<sub>R</sub>

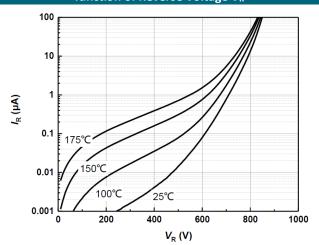


Fig. 3 • Diode Forward Current I<sub>F</sub> as function of Case Temperature T<sub>C</sub> (D = Duty Cycle)

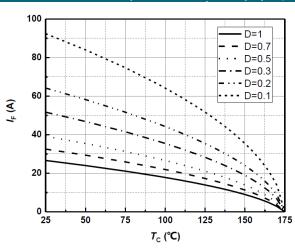


Fig. 4 • Typical Capacitance C as function of Reverse Voltage V<sub>R</sub>, C = f(V<sub>R</sub>), T<sub>J</sub> = 25°C, f = 1MHz

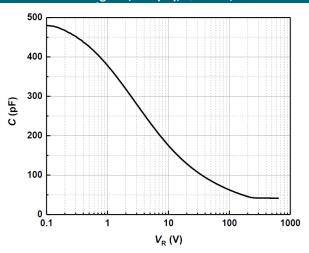


Fig. 5 • Typical Reverse Charge Q<sub>C</sub> as function of Reverse Voltage V<sub>R</sub>

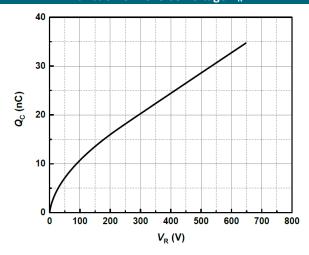
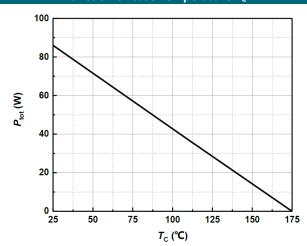


Fig. 6 • Power Dissipation P<sub>TOT</sub> as function of Case Temperature T<sub>C</sub>



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## REFERENCE DATA A TYPICAL PERFORMANCE

Fig. 7 • Capacitance Stored Energy

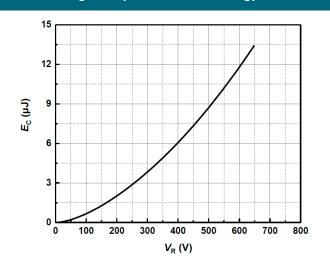
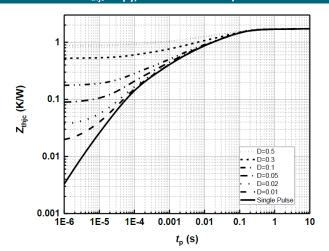
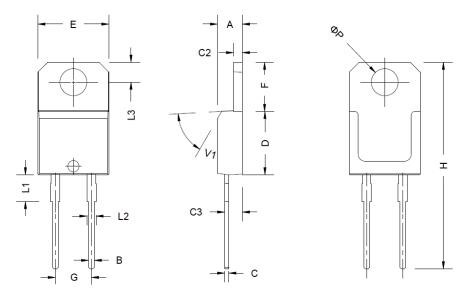


Fig. 8 • Maximum Transient Thermal Impedance, Z<sub>thjc</sub> = f(t), Parameter: D = t/T





# **PACKAGE OUTLINE**





Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
Α	4.40	4.50	4.60
В	0.61	0.75	0.88
С	0.46	0.58	0.70
C2	1.21	1.265	1.32
C3	2.40	2.56	2.72
D	8.60	9.15	9.70
Е	9.80	10.10	10.40
F	6.55	6.75	6.95

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
G		5.08 BSC	
Н	28.00	28.90	29.80
L1	-	3.75	-
L2	1.14	-	1.70
L3	2.65	2.80	2.95
V1	-	45°	-
ØР	-	-	3.88

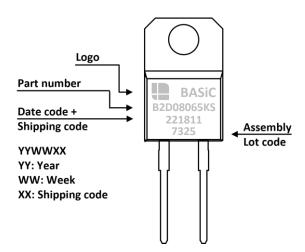
## TO-220 ISO-2L package ▲ Epoxy meets UL94-V0

# **ORDERING INFORMATION**

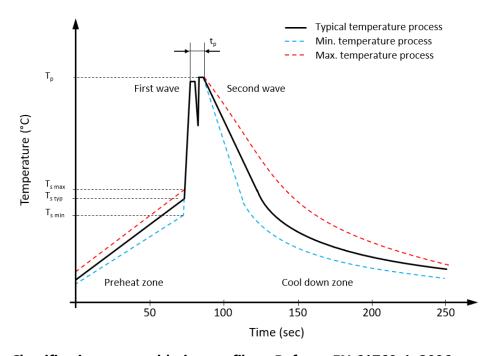
Part Number	Package	Packing	Tube Qty.	Inner Box Qty.	Outer Box Qty.
B2D08065KS	TO-220 ISO-2L	Tube	50pcs	500pcs	5,000pcs



#### **PART MARKING**



# RECOMMENDED WAVE SOLDERING PROFILE & THT PACKAGE



# Classification wave soldering profile ▲ Refer to EN 61760-1: 2006

Profile Features		Value ▲ Sn-Pb Assembly	Value ▲ Pb-free Assembly
Preheat temperature min.	$T_{smin}$	100 °C	100 °C
Preheat temperature typical	T <sub>s typ</sub>	120 °C	120 °C
Preheat temperature max.	$T_{smax}$	130 °C	130 °C
Preheat time $t_s$ from $T_{smin}$ to $T_{smax}$	ts	70 seconds	70 seconds
Peak temperature	$T_p$	235 °C to 260 °C	245 °C to 260 °C
Time of actual peak temperature	tp	Max. 10 seconds Max. 5 second each wave	Max. 10 seconds Max. 5 second each wave
Ramp-down date min.		~ 2 °C/second	~ 2 °C/second
Ramp-down rate typical		~ 3.5 °C/second	~ 3.5 °C/second
Ramp-down rate max.		~ 5 °C/second	~ 5 °C/second
Time 25°C to 25°C		4 minutes	4 minutes

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#### **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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